

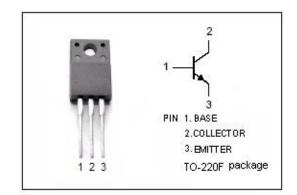
# **isc Silicon NPN Power Transistor**

#### **DESCRIPTION**

- · High Breakdown Voltage and High Reliability
- · High Switching Speed
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

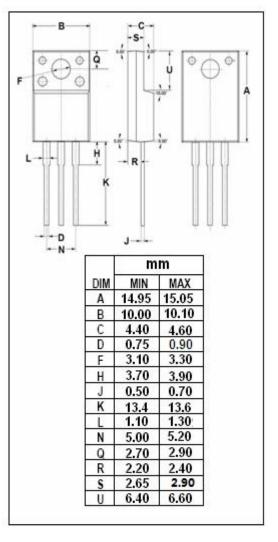
#### **APPLICATIONS**

• Designed for switching regulator applications.



# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	1100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
Ic	Collector Current-Continuous	3	А
Ісм	Collector Current-Pulse	10	А
I <sub>B</sub>	Base Current-Continuous	1.5	А
Pc	Collector Power Dissipation @T <sub>C</sub> =25°C	30	W
TJ	Junction Temperature	150	${\mathbb C}$
T <sub>stg</sub>	Storage Temperature	-55~150	°C





### isc Silicon NPN Power Transistor

2SC3752

#### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C$ = 5mA; $R_{BE}$ = $\infty$	800			V	
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	1100			V	
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	7			V	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1.5A; I <sub>B</sub> = 0.3A			2.0	V	
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1.5A; I <sub>B</sub> = 0.3A			1.5	V	
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 800V ; I <sub>E</sub> = 0			10	μА	
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			10	μА	
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.2A; V <sub>CE</sub> = 5V	10		40		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	8				
	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.2A; V <sub>CE</sub> = 10V		15		MHz	
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f= 1MHz		60		pF	
Switching times							
ton	Turn-on Time				0.5	μS	
t <sub>stg</sub>	Storage Time	$I_{C}$ = 2A , $I_{B1}$ = 0.4A; $I_{B2}$ = -0.8A; $I_{L}$ = 200 $\Omega$ , $V_{CC}$ = 400V			3.0	μS	
t <sub>f</sub>	Fall Time				0.3	μS	

## ♦ h<sub>FE-1</sub> Classifications

K	L	M
10-20	15-30	20-40

#### **NOTICE:**

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